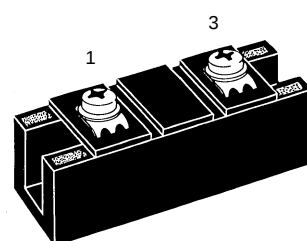
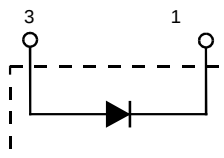


Fast Recovery Epitaxial Diode (FRED) Module

MEO 550-02 DA

$V_{RRM} = 200\text{ V}$
 $I_{FAVM} = 582\text{ A}$
 $t_{rr} = 150\text{ ns}$

V_{RSM}	V_{RRM}	Type
V	V	
200	200	MEO 550-02DA



Symbol	Test Conditions	Maximum Ratings	
I_{FRMS}	$T_C = 75^\circ\text{C}$	822	A
I_{FAVM} ①	$T_C = 75^\circ\text{C}$; rectangular, $d = 0.5$	582	A
I_{FRM}	$t_p < 10\text{ }\mu\text{s}$; rep. rating, pulse width limited by T_{VJM}	2880	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t = 10\text{ ms}$ (50 Hz), sine	4800	A
	$t = 8.3\text{ ms}$ (60 Hz), sine	5280	A
	$T_{VJ} = 150^\circ\text{C}$; $t = 10\text{ ms}$ (50 Hz), sine	4320	A
	$t = 8.3\text{ ms}$ (60 Hz), sine	4750	A
I^2t	$T_{VJ} = 45^\circ\text{C}$; $t = 10\text{ ms}$ (50 Hz), sine	115200	A ² s
	$t = 8.3\text{ ms}$ (60 Hz), sine	117100	A ² s
	$T_{VJ} = 150^\circ\text{C}$; $t = 10\text{ ms}$ (50 Hz), sine	93300	A ² s
	$t = 8.3\text{ ms}$ (60 Hz), sine	94800	A ² s
T_{VJ}		-40...+150	°C
T_{stg}		-40...+125	°C
T_{Smax}		110	°C
P_{tot}	$T_C = 25^\circ\text{C}$	1750	W
V_{ISOL}	50/60 Hz, RMS $t = 1\text{ min}$	3000	V~
	$I_{ISOL} \leq 1\text{ mA}$ $t = 1\text{ s}$	3600	V~
M_d	Mounting torque (M6)	2.25-2.75/20-25	Nm/lb.in.
	Terminal connection torque (M6)	4.50-5.50/40-48	Nm/lb.in.
d_s	Creep distance on surface	12.7	mm
d_A	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²
Weight		150	g

Features

- International standard package with DCB ceramic base plate
- Planar passivated chips
- Short recovery time
- Low switching losses
- Soft recovery behaviour
- Isolation voltage 3600 V~
- UL registered E 72873

Applications

- Antiparallel diode for high frequency switching devices
- Free wheeling diode in converters and motor control circuits
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

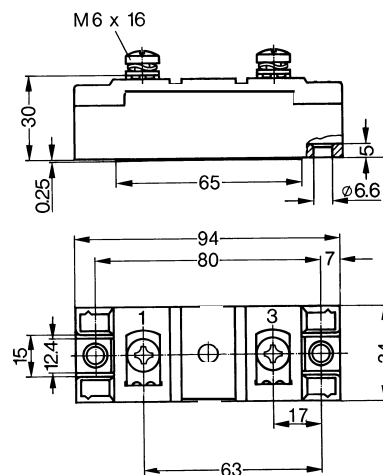
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Symbol	Test Conditions		Characteristic Values (per diode)		
			typ.	max.	
I _R	T _{VJ} = 25°C	V _R = V _{RRM}	5	mA	
	T _{VJ} = 25°C	V _R = 0.8 • V _{RRM}	4	mA	
	T _{VJ} = 125°C	V _R = 0.8 • V _{RRM}	160	mA	
V _F	I _F = 300 A;	T _{VJ} = 125°C	0.84	V	
		T _{VJ} = 25°C	1.10	V	
	I _F = 520 A;	T _{VJ} = 125°C	1.08	V	
		T _{VJ} = 25°C	1.25	V	
V _{T0}	For power-loss calculations only		0.52	V	
r _T			1.06	mΩ	
R _{thJH}	DC current		0.114	K/W	
R _{thJC}	DC current		0.071	K/W	
t _{rr}	I _F = 500 A V _R = 100 V -di/dt = 200 A/μs	T _{VJ} = 100°C T _{VJ} = 25°C T _{VJ} = 100°C	150	200	ns
I _{RM}				9	A
				15	A

① I_{FAVM} rating includes reverse blocking losses at T_{VJM} , $V_R = 0.6 V_{RRM}$, duty cycle $d = 0.5$
 Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions

Dimensions in mm (1 mm = 0.0394")



911

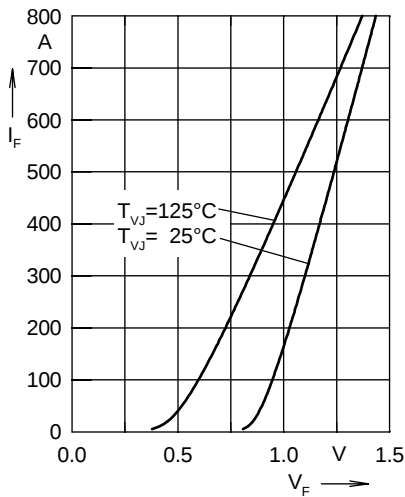


Fig. 1 Forward current I_F versus max. voltage drop V_F per leg

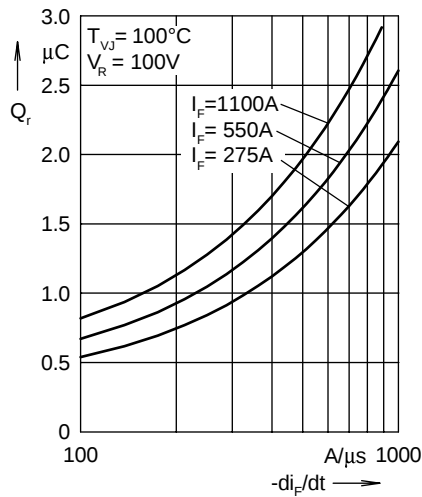


Fig. 2 Typ. reverse recovery charge Q_r versus $-di_F/dt$

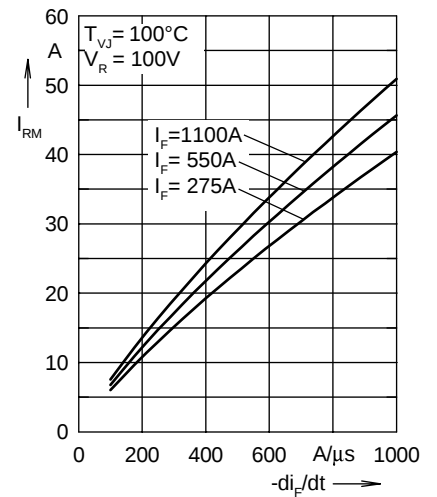


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

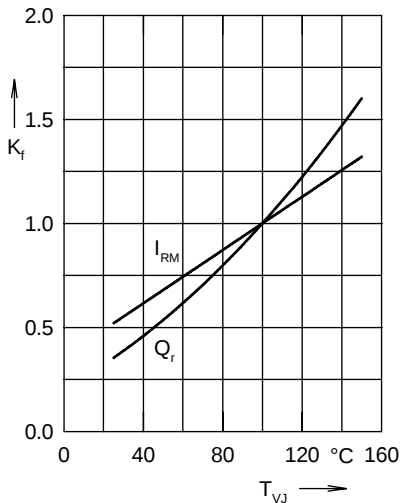


Fig. 4 Dynamic parameters Q_r , I_{RM} versus junction temperature T_{VJ}

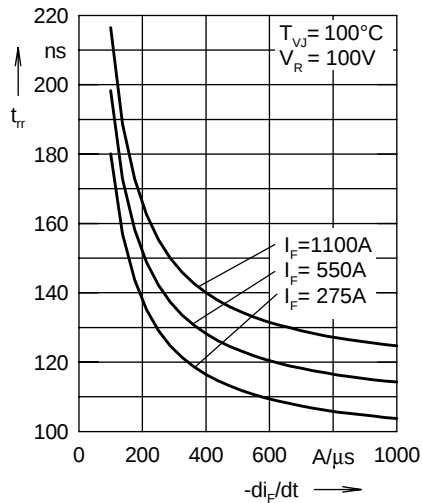


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

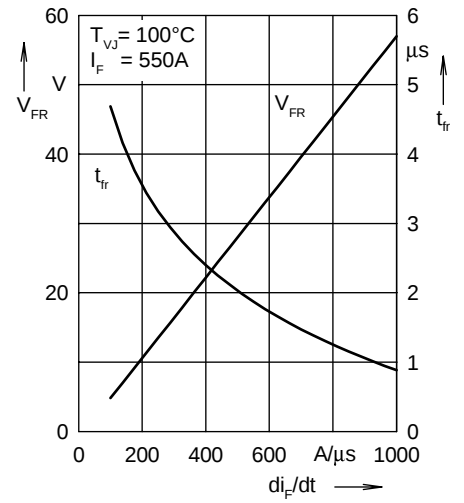


Fig. 6 Typ. peak forward voltage V_{FR} and t_{rr} versus di_F/dt

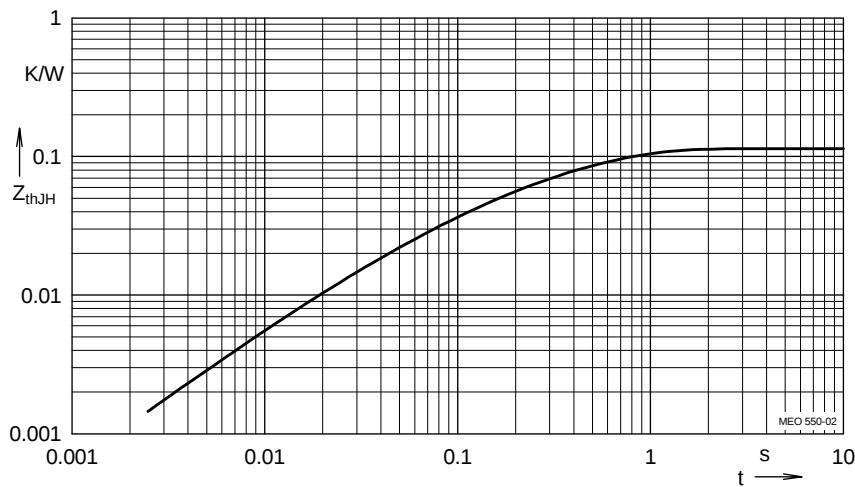


Fig. 7 Transient thermal impedance junction to heatsink

Constants for Z_{thJS} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.001	0.08
2	0.004	0.024
3	0.027	0.112
4	0.082	0.464